

Thyristors

BT151F series

GENERAL DESCRIPTION

Glass passivated thyristors in a full pack, plastic envelope, intended for use in applications requiring high bidirectional blocking voltage capability and high thermal cycling performance. Typical applications include motor control, industrial and domestic lighting, heating and static switching.

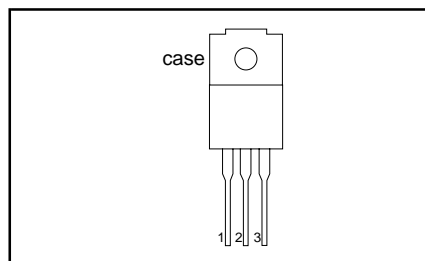
QUICK REFERENCE DATA

SYMBOL	PARAMETER	MAX.	MAX.	MAX.	UNIT
V_{DRM} , V_{RRM}	Repetitive peak off-state voltages	500 500	650 650	800 800	V
$I_{T(AV)}$	Average on-state current	5.7	5.7	5.7	A
$I_{T(RMS)}$	RMS on-state current	9	9	9	A
I_{TSM}	Non-repetitive peak on-state current	100	100	100	A

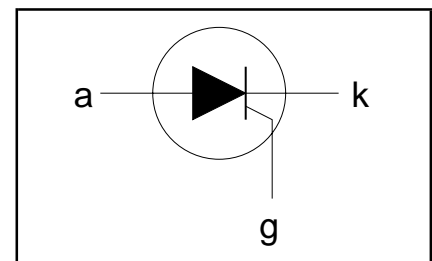
PINNING - SOT186

PIN	DESCRIPTION
1	cathode
2	anode
3	gate
case	isolated

PIN CONFIGURATION



SYMBOL



LIMITING VALUES

Limiting values in accordance with the Absolute Maximum System (IEC 134).

SYMBOL	PARAMETER	CONDITIONS	MIN.	MAX.			UNIT
				-500	-650	-800	
V_{DRM} , V_{RRM}	Repetitive peak off-state voltages		-	500 ¹	650 ¹	800	V
$I_{T(AV)}$	Average on-state current	half sine wave; $T_{hs} \leq 87^\circ\text{C}$	-	5.7			A
$I_{T(RMS)}$	RMS on-state current	all conduction angles	-	9			A
I_{TSM}	Non-repetitive peak on-state current	half sine wave; $T_j = 125^\circ\text{C}$ prior to surge; with reapplied $V_{DRM(max)}$	-	100			A
I^2t	I^2t for fusing	$t = 10\text{ ms}$	-	110			A
dI_T/dt	Repetitive rate of rise of on-state current after triggering	$t = 8.3\text{ ms}$	-	50			A ² s
		$t = 10\text{ ms}$	-	50			A/ μs
I_{GM}	Peak gate current	$I_{TM} = 20\text{ A}$; $I_G = 50\text{ mA}$;	-	2			A
V_{GM}	Peak gate voltage	$dI_G/dt = 50\text{ mA}/\mu\text{s}$	-	5			V
V_{RGM}	Peak reverse gate voltage		-	5			V
P_{GM}	Peak gate power		-	5			W
$P_{G(AV)}$	Average gate power	over any 20 ms period	-	0.5			W
T_{stg}	Storage temperature		-40	150			$^\circ\text{C}$
T_j	Operating junction temperature		-	125			$^\circ\text{C}$

¹ Although not recommended, off-state voltages up to 800V may be applied without damage, but the thyristor may switch to the on-state. The rate of rise of current should not exceed 15 A/ μs .

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ISOLATION LIMITING VALUE & CHARACTERISTIC $T_{hs} = 25\text{ °C}$ unless otherwise specified

SYMBOL	PARAMETER	CONDITIONS	MIN.	TYP.	MAX.	UNIT
V_{isol}	Repetitive peak voltage from all three terminals to external heatsink	R.H. \leq 65% ; clean and dustfree	-		1500	V
C_{isol}	Capacitance from T2 to external heatsink	$f = 1\text{ MHz}$	-	12	-	pF

THERMAL RESISTANCES

SYMBOL	PARAMETER	CONDITIONS	MIN.	TYP.	MAX.	UNIT
$R_{th\ j-hs}$	Thermal resistance junction to heatsink	with heatsink compound	-	-	4.5	K/W
$R_{th\ j-a}$	Thermal resistance junction to ambient	without heatsink compound in free air	-	55	6.5	K/W

STATIC CHARACTERISTICS $T_j = 25\text{ °C}$ unless otherwise stated

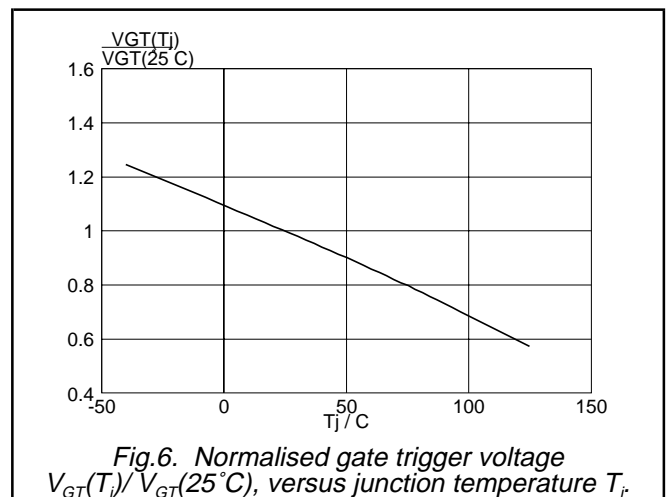
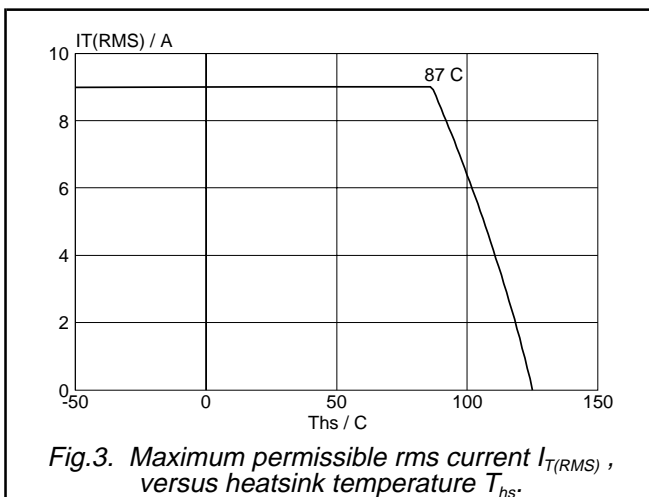
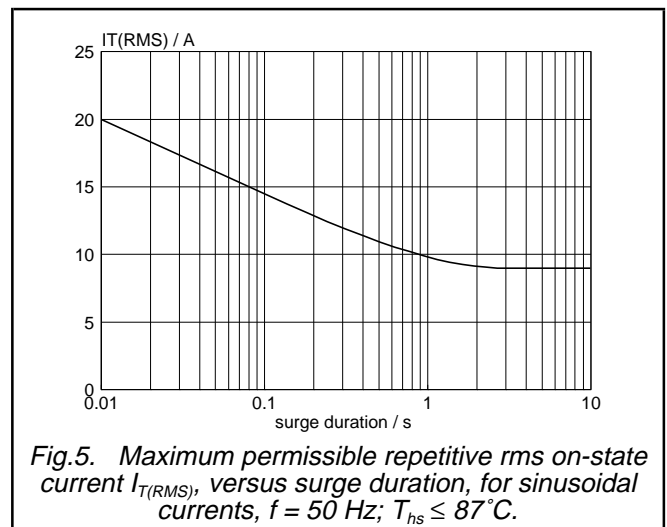
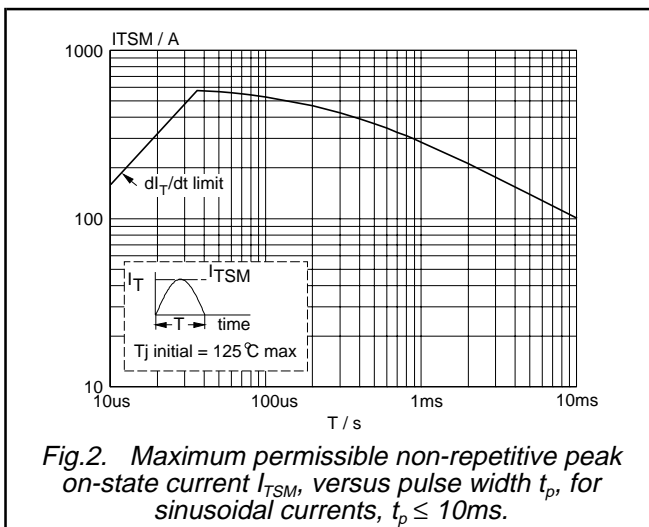
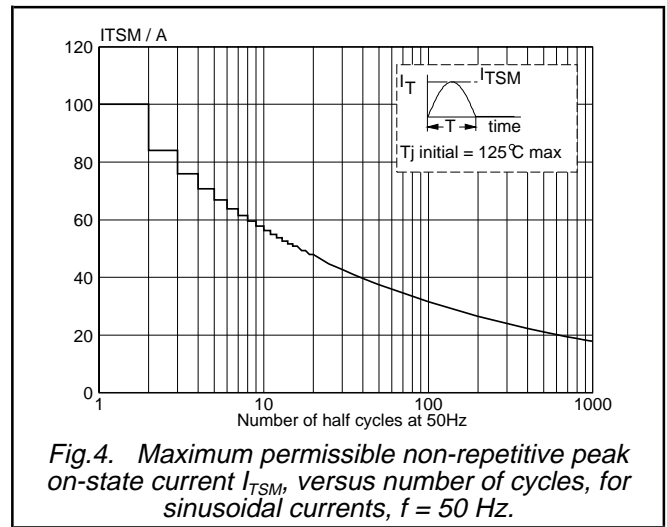
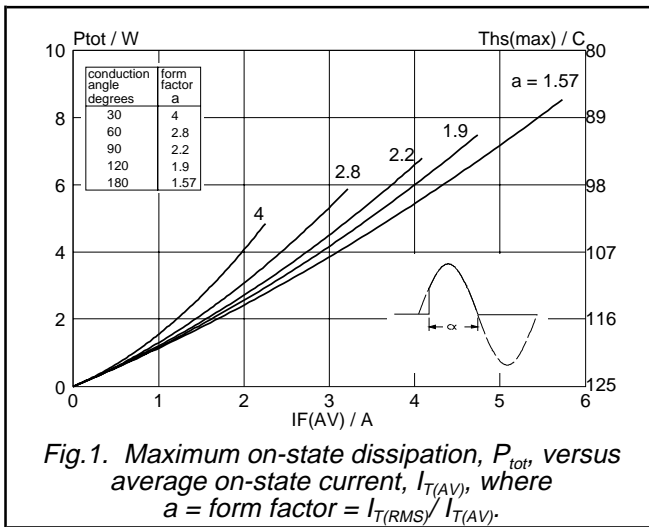
SYMBOL	PARAMETER	CONDITIONS	MIN.	TYP.	MAX.	UNIT
I_{GT}	Gate trigger current	$V_D = 12\text{ V}; I_T = 0.1\text{ A}$	-	2	15	mA
I_L	Latching current	$V_D = 12\text{ V}; I_{GT} = 0.1\text{ A}$	-	10	40	mA
I_H	Holding current	$V_D = 12\text{ V}; I_{GT} = 0.1\text{ A}$	-	7	20	mA
V_T	On-state voltage	$I_T = 23\text{ A}$	-	1.4	1.75	V
V_{GT}	Gate trigger voltage	$V_D = 12\text{ V}; I_T = 0.1\text{ A}$	-	0.6	1.5	V
I_D, I_R	Off-state leakage current	$V_D = V_{DRM(max)}; I_T = 0.1\text{ A}; T_j = 125\text{ °C}$ $V_D = V_{DRM(max)}; V_R = V_{RRM(max)}; T_j = 125\text{ °C}$	0.25	0.4	-	V
			-	0.1	0.5	mA

DYNAMIC CHARACTERISTICS $T_j = 25\text{ °C}$ unless otherwise stated

SYMBOL	PARAMETER	CONDITIONS	MIN.	TYP.	MAX.	UNIT
dV_D/dt	Critical rate of rise of off-state voltage	$V_{DM} = 67\% V_{DRM(max)}; T_j = 125\text{ °C};$ exponential waveform				
		Gate open circuit $R_{GK} = 100\ \Omega$	50	130	-	V/ μ s
t_{gt}	Gate controlled turn-on time	$I_{TM} = 40\text{ A}; V_D = V_{DRM(max)}; I_G = 0.1\text{ A};$ $di_G/dt = 5\text{ A}/\mu\text{s}$	200	1000	-	V/ μ s
t_q	Circuit commutated turn-off time	$V_D = 67\% V_{DRM(max)}; T_j = 125\text{ °C};$ $I_{TM} = 20\text{ A}; V_R = 25\text{ V}; di_{TM}/dt = 30\text{ A}/\mu\text{s};$ $dV_D/dt = 50\text{ V}/\mu\text{s}; R_{GK} = 100\ \Omega$	-	70	-	μ s

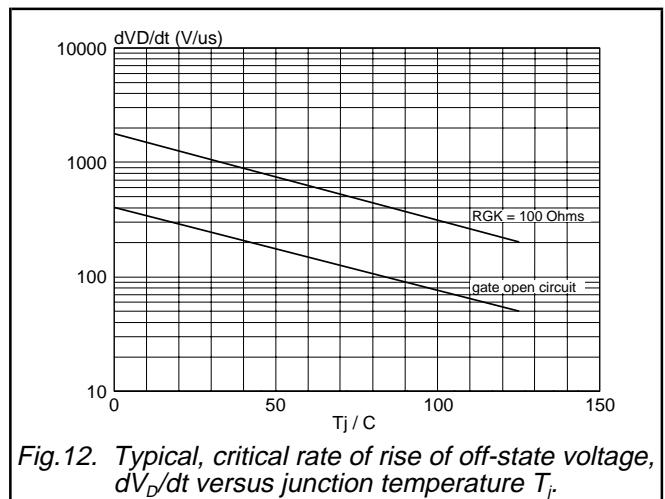
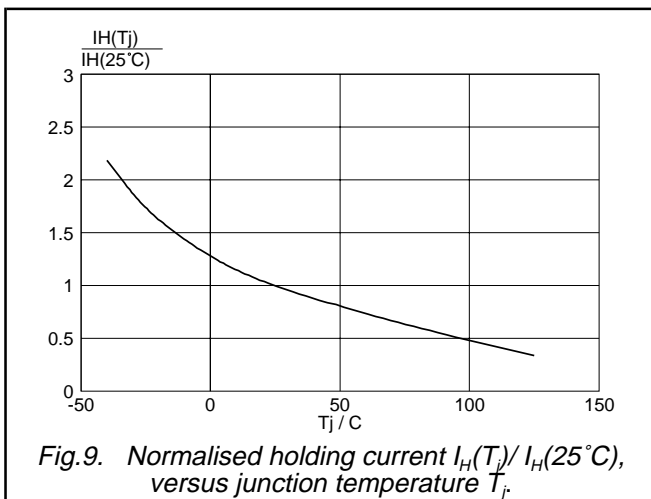
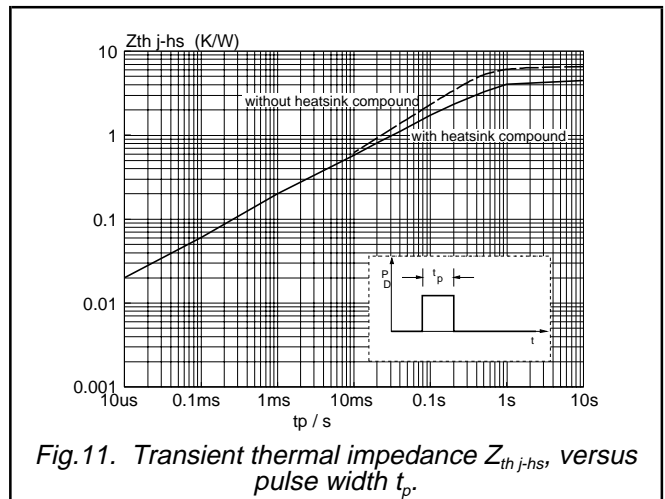
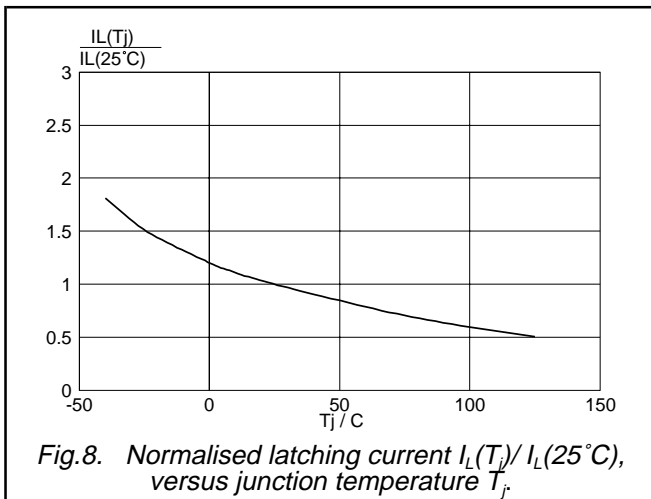
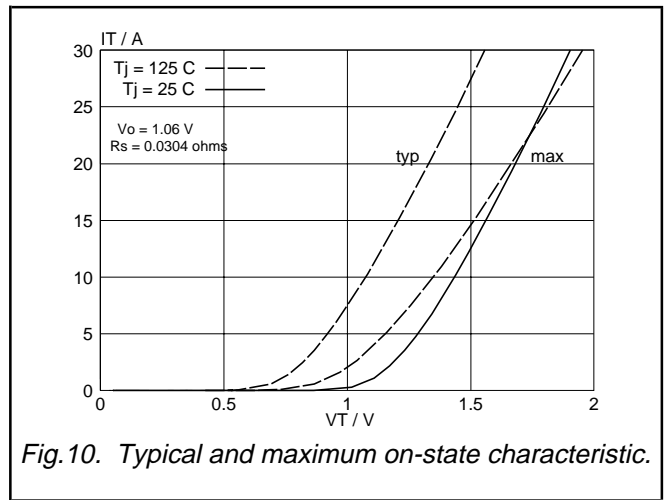
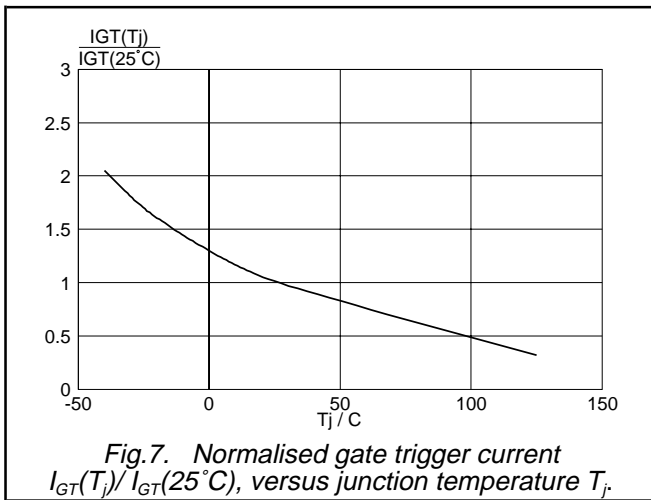
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DEFINITIONS

Data sheet status	
Objective specification	This data sheet contains target or goal specifications for product development.
Preliminary specification	This data sheet contains preliminary data; supplementary data may be published later.
Product specification	This data sheet contains final product specifications.
Limiting values	
Limiting values are given in accordance with the Absolute Maximum Rating System (IEC 134). Stress above one or more of the limiting values may cause permanent damage to the device. These are stress ratings only and operation of the device at these or at any other conditions above those given in the Characteristics sections of this specification is not implied. Exposure to limiting values for extended periods may affect device reliability.	
Application information	
Where application information is given, it is advisory and does not form part of the specification.	
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